

Title (en)

METHOD FOR PRODUCING DEFINED POLYCRYSTALLINE SILICON AREAS IN AN AMORPHOUS SILICON LAYER

Title (de)

VERFAHREN ZUR HERSTELLUNG DEFINIERTER POLYKRISTALLINER SILIZIUM-BEREICHE IN EINER AMORPHEN SILIZIUMSCHICHT

Title (fr)

PROCEDE DE FABRICATION DE ZONES DE SILICIUM POLYCRISTALLIN DEFINIES DANS UNE COUCHE DE SILICIUM AMORPHE

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Application

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Abstract (en)

[origin: WO0159818A1] The invention relates to a method for producing defined polycrystalline silicon areas, especially for creating conductive areas, comprising the following steps: (a) a substrate (10) is provided with an insulating layer (12) and a layer made of doped amorphous silicon (14); b) said structure is exposed to electromagnetic radiation (20) with the aid of a laser source (18) in order to produce the electrically conductive areas (26); c) a shadow mask (22) is placed in between the substrate provided with the doped amorphous silicon layer (14) and the laser source (18) in order to define the contours of the electrically conductive areas (26).

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